

# Low $V_{CE(sat)}$ transistor (strobe flash)

## 2SD2098 / 2SD2118 / 2SD2097

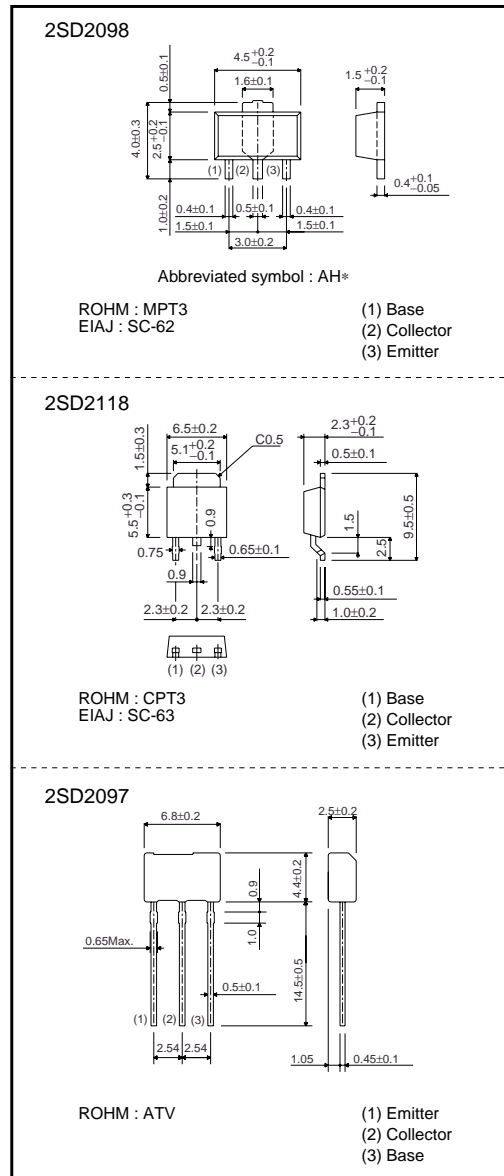
●Features

- 1) Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = 0.25V$  (Typ.)  
 $(I_C/I_B = 4A / 0.1A)$
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SB1386 / 2SB1412 / 2SB1326.

●Structure

Epitaxial planar type  
 NPN silicon transistor

●External dimensions (Units : mm)



\* Denotes hFE

## Transistors

## ●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V <sub>CB0</sub>	50	V
Collector-emitter voltage		V <sub>CEO</sub>	20	V
Emitter-base voltage		V <sub>EBO</sub>	6	V
Collector current		I <sub>c</sub>	5	A(DC)
		I <sub>cP</sub>	10	A(Pulse) *1
Collector power dissipation	2SD2098	P <sub>c</sub>	0.5	W *2
			2	
	1			
	2SD2118		10	W(T <sub>c</sub> =25°C)
2SD2097	1	W *3		
Junction temperature		T <sub>j</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55~+150	°C

\*1 Single pulse P<sub>w</sub>=10ms

\*2 When mounted on a 40×40×0.7 mm ceramic board.

\*3 Printed circuit board glass epoxy board, 1.6 mm thick with copper plating 100mm<sup>2</sup> or larger.

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	50	–	–	V	I <sub>c</sub> =50μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	20	–	–	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	–	–	V	I <sub>E</sub> =50μA
Collector cutoff current	I <sub>cBO</sub>	–	–	0.5	μA	V <sub>CB</sub> =40V
Emitter cutoff current	I <sub>EBO</sub>	–	–	0.5	μA	V <sub>EB</sub> =5V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	–	0.25	1.0	V	I <sub>c</sub> /I <sub>B</sub> =4A/0.1A *
DC current transfer ratio	h <sub>FE</sub>	120	–	390	–	V <sub>CE</sub> =2V, I <sub>c</sub> =0.5A *
Transition frequency	f <sub>T</sub>	–	150	–	MHz	V <sub>CE</sub> =6V, I <sub>E</sub> =-50mA, f=100MHz
Output capacitance	C <sub>ob</sub>	–	30	–	pF	V <sub>CE</sub> =20V, I <sub>E</sub> =0A, f=1MHz

\* Measured using pulse current.

●Packaging specifications and h<sub>FE</sub>

Type	h <sub>FE</sub>	Package	Taping		
		Code	T100	TL	TV2
		Basic ordering unit (pieces)	1000	2500	2500
2SD2098	QR		○	–	–
2SD2118	QR		–	○	–
2SD2097	QR		–	–	○

h<sub>FE</sub> values are classified as follows :

Item	Q	R
h <sub>FE</sub>	120~270	180~390

Transistors

● Electrical characteristic curves

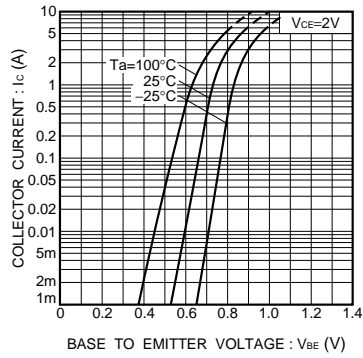


Fig.1 Grounded emitter propagation characteristics

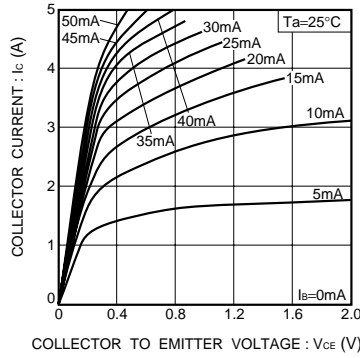


Fig.2 Grounded emitter output characteristics

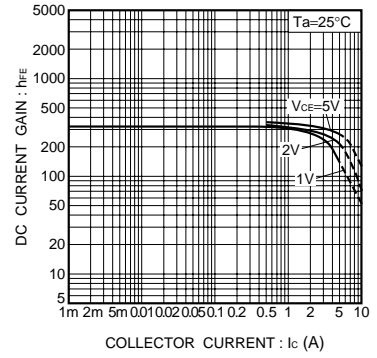


Fig.3 DC current gain vs. collector current ( I )

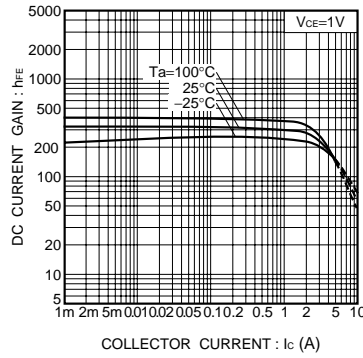


Fig.4 DC current gain vs. collector current ( II )

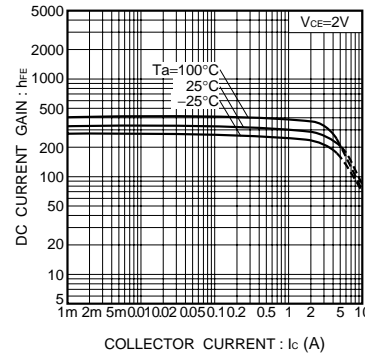


Fig.5 DC current gain vs. collector current ( III )

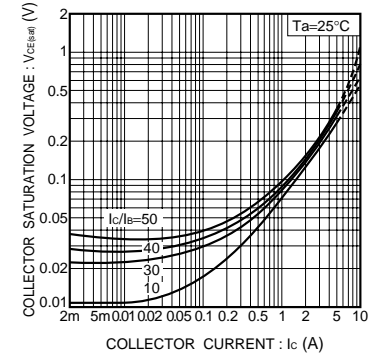


Fig.6 Collector-emitter saturation voltage vs. collector current ( I )

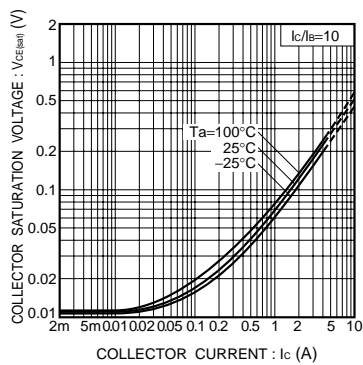


Fig.7 Collector-emitter saturation voltage vs. collector current ( II )

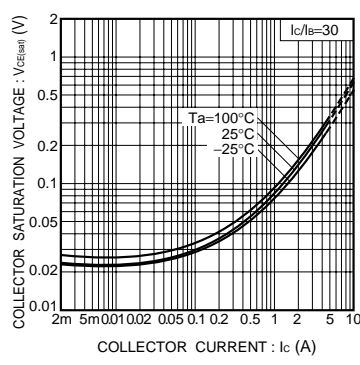


Fig.8 Collector-emitter saturation voltage vs. collector current ( III )

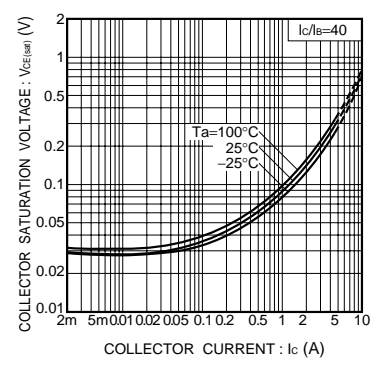


Fig.9 Collector-emitter saturation voltage vs. collector current ( IV )

Transistors

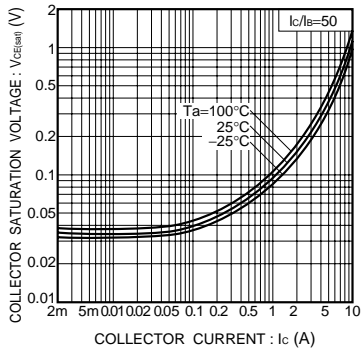


Fig.10 Collector-emitter saturation voltage vs. collector current (V)

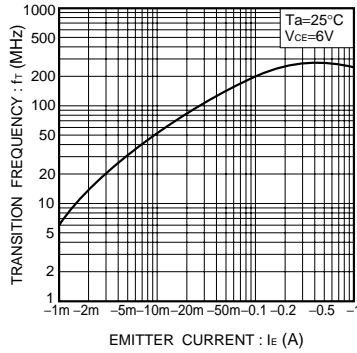


Fig.11 Gain bandwidth product vs. emitter current

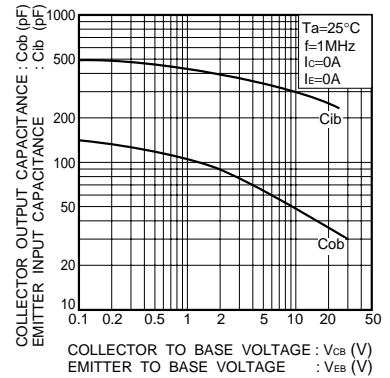


Fig.12 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

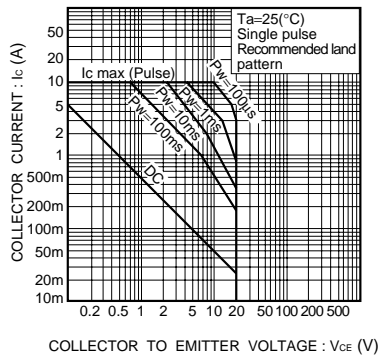


Fig.13 Safe operating area (2SD2098)

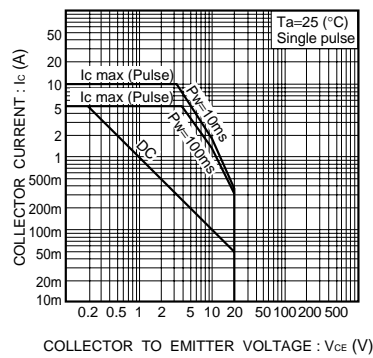


Fig.14 Safe operating area (2SD2118)